Thyristor High Voltage, Phase Control SCR, 80 A



PR

Package

Circuit configuration

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3	0 0
TO-247AD 3L	1 (K) (G) 3
RIMARY CHARACTE	RISTICS
I _{T(AV)}	80 A
V _{DRM} /V _{RRM}	1600 V
V _{TM} (typ.)	1.16 V
I _{GT}	100 mA
TJ	-40 °C to +150 °C

TO-247AD 3L

Single SCR

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 150 °C maximum operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-80TPS16L high voltage series of silicon controlled rectifiers are specifically designed for medium power switching, and phase control applications. The glass passivation technology used, has reliable operation up to 150 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V _{RRM} /V _{DRM}		1600	V				
On-state voltage	V _T	80 A, T _J = 125 °C, typical	1.16	v				
Average rectified forward current	I _{T(AV)}		80					
Maximum continuous RMS on-state current	I _{RMS}		126	А				
Non-repetitive peak surge current	I _{TSM}		1000					
Maximum rate of rise	dV/dt		1000	V/µs				
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-40 to +150	°C				

VOLTAGE RATINGS							
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	TYP. I _{RRM} /I _{DRM} AT 125 °C mA				
VS-80TPS16L-M3	1600	1700	10				



VS-80TPS16L-M3



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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T_{C} = 113 °C, 180° conduction half sine v	T_{C} = 113 °C, 180° conduction half sine wave		80	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}		-	126	А	
Peak one sucle non repetitive surge surger		10 ms sine pulse, rated V_{RRM} applied		-	840	
Peak, one-cycle non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	Initial T _J =	-	1000	
12t for funing	l ² t	10 ms sine pulse, rated V_{RRM} applied	T _J maximum	-	3536	A ² s
I ² t for fusing	1 - t	10 ms sine pulse, no voltage reapplied		-	5000	A∸s
I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplie	d, T _J = 125 °C	-	50 000	A²√s
		80 A, T _J = 25 °C		1.22	1.40	
	V _T	160 A, T _J = 25 °C		1.48	1.66	v
On-state voltage		80 A, T _J = 125 °C		1.16	1.24	
		160 A, T _J = 125 °C			1.62	
Low level value of threshold voltage	V _{T01}	T 450.80		-	0.80	
High level value of threshold voltage	V _{T02}	T _J = 150 °C		-	0.89	V
Low level value of on-state slope resistance	r _{t1}	T 150.00		-	4.82	
High level value of on-state slope resistance	r _{t2}	T _J = 150 °C		-	4.51	mΩ
Rate of rise of turned-on current	dl/dt	T_{J} = 125 °C, V_{R} = 1000 V, I_{T} = 100 A, I_{gt} V_{GT} = 2.5 V	= 450 mA,	-	500	A/µs
Holding current	Ι _Η	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$		-	200	
Latching current	١L			-	400	mA
	1 /1	T _J = 25 °C		50	200	μA
Reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 125 °C			60	mA
Rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V _{DRM} ,	R _g -k = open	-	1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS	TYP.	MAX.	UNITS
Peak gate power	P_{GM}	10 ms sino puls	se, no voltage reapplied	-	10	w
Average gate power	P _{G(AV)}		-	2.5	vv	
Peak gate current	I _{GM}				2.5	А
Peak negative gate voltage	-V _{GM}				10	v
Required DC gate voltage to trigger	V _{GT}	$T_J = 25 \ ^\circ C$	Anode supply = 6 V resistive load	-	1.5	v
Required DC gate to trigger	I _{GT}	T _J = 25 °C Anode supply = 6 V resistive load		-	100	mA
DC gate voltage not to trigger	V_{GD}			-	0.20	V
DC gate current not to trigger	I _{GD}	$i_{\rm J} = i25$ C, V	T_J = 125 °C, V_{DRM} = 80 % rated value			mA

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS
Turn-on time	t _{gt}	I_T = 80 A, V_D = 50 % V_{DRM},I_{gt} = 300 mA, T_J = 25 °C	2	-	
Turn-off time	t _q	$\label{eq:IT} \begin{array}{l} I_T = 80 \; A, \; V_D = 80 \; \% \; V_{DRM}, \; dV/dt = 20 \; V/\mu s, \; t_p = 200 \; \mu s \\ I_{gt} = 100 \; mA, \; dI/dt = 10 \; A/\mu s, \; V_R = 100 \; V, \; T_J = 150 \; ^\circ C \end{array}$	150	-	μs

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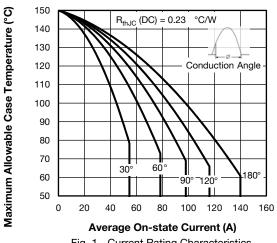
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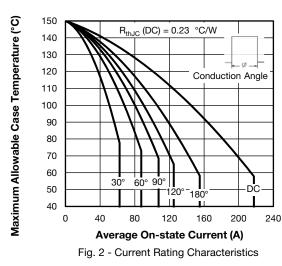
THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	MBOL TEST CONDITIONS			UNITS		
Maximum operating junction and storage t range	laximum operating junction and storage temperature			-40	150	°C		
Maximum thermal resistance, junction to case		R _{thJC}		-	0.23			
Maximum thermal resistance, junction to ambient		R _{thJA}		-	40	°C/W		
Typical thermal resistance, case to heatsin	k	R _{thCS}	Mounting surface, smooth, and greased	0.	20			
Approximate weight				6 (0).21)	g (oz.)		
Mounting torque	minimum			6	(5)	kgf ⋅ cm		
Mounting torque	maximum			12 (10)		(lbf ⋅ in)		
Marking device			Case style TO-247AD 3L		80TPS1	6L		

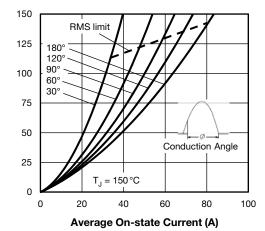
DEVICE	SINE HALF-WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION					ION	UNITS				
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-80TPS16L-M3	0.031	0.036	0.040	0.042	0.044	0.028	0.036	0.038	0.040	0.042	°C/W

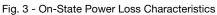
Max. Average On-state Power Loss (W)











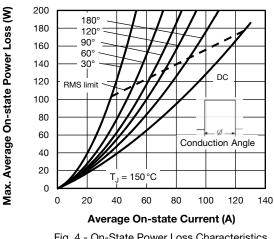


Fig. 4 - On-State Power Loss Characteristics

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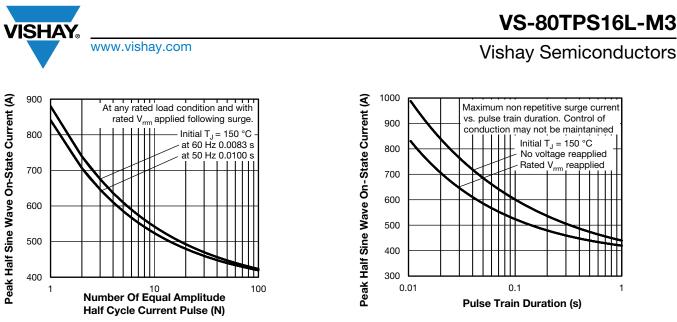


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

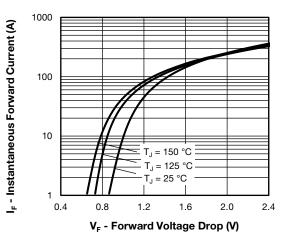
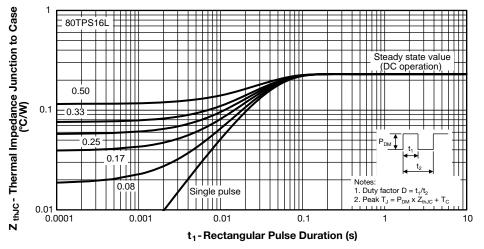


Fig. 7 - On-State Voltage Drop Characteristics





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ORDERING INFORMATION TABLE

Device code	VS-	80	т	Р	s	16	L	-M3
	1	2	3	4	5	6	7	8
	2	- Cur	hay Serr rrent coc cuit conf	le (80 =	80 A)	oduct		
	4	- P=	thyristo TO-247 e of silio	packag	je			
	7	- Voli - Pac	standar tage coo ckage L s = halog	le (16 = = long le	1600 V ead)	ant, and	l termina

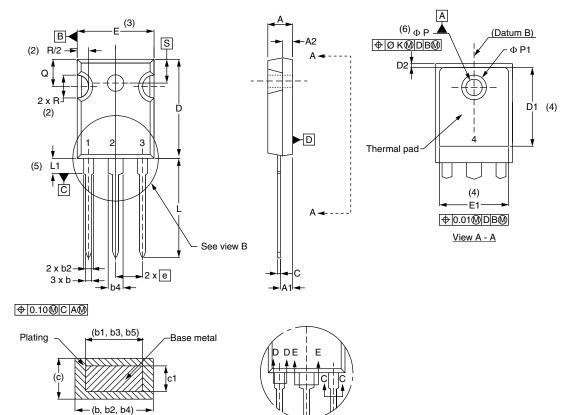
ORDERING INFORMATION (example)							
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-80TPS16L-M3	25	500	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95626					
Part marking information	www.vishay.com/doc?95007				



TO-247AD 3L

DIMENSIONS in millimeters and inches



View B

	Section C - C, D - D, E - E										
SYMBOL	MILLIM	IETERS	INC	NOTES							
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NUTES						
А	4.65	5.31	0.183	0.209							
A1	2.21	2.59	0.087	0.102							
A2	1.50	2.49	0.059	0.098							
b	0.99	1.40	0.039	0.055							
b1	0.99	1.35	0.039	0.053							
b2	1.65	2.39	0.065	0.094							
b3	1.65	2.34	0.065	0.092							
b4	2.59	3.43	0.102	0.135							
b5	2.59	3.38	0.102	0.133							
С	0.38	0.89	0.015	0.035							
c1	0.38	0.84	0.015	0.033							
D	19.71	20.70	0.776	0.815	3						
D1	13.08	-	0.515	-	4						

(4)

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
Е	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46 BSC		0.215 BSC		
ØК	0.254		0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- ⁽³⁾ Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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